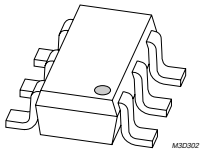


PMN34LN

1. Product profile

1.1 Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

Product availability:

PMN34LN in SOT457 (TSOP6).

1.2 Features

- Low on-state resistance in small surface mount package.

1.3 Applications

- DC-to-DC primary side.

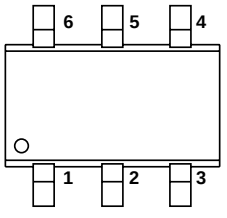
1.4 Quick reference data

- $V_{DS} \leq 20$ V
- $I_D \leq 5.7$ A
- $P_{tot} \leq 1.75$ W
- $R_{DSon} \leq 34$ mΩ

2. Pinning information

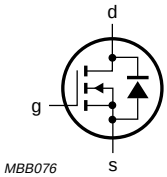
Table 1: Pinning - SOT457 (TSOP6), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1,2,5,6	drain (d)		
3	gate (g)		
4	source (s)		



Top view MBK092

SOT457 (TSOP6)



3. Limiting values

Table 2: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	25 °C ≤ T_j ≤ 150 °C	-	20	V
V_{DGR}	drain-gate voltage (DC)	25 °C ≤ T_j ≤ 150 °C; R_{GS} = 20 kΩ	-	20	V
V_{GS}	gate-source voltage (DC)		-	±15	V
I_D	drain current (DC)	T_{sp} = 25 °C; V_{GS} = 10 V; Figure 2 and 3	-	5.7	A
		T_{sp} = 100 °C; V_{GS} = 10 V; Figure 2	-	3.6	A
I_{DM}	peak drain current	T_{sp} = 25 °C; pulsed; t_p ≤ 10 µs; Figure 3	-	22.9	A
P_{tot}	total power dissipation	T_{sp} = 25 °C; Figure 1	-	1.75	W
T_{stg}	storage temperature		–55	+150	°C
T_j	junction temperature		–55	+150	°C
Source-drain diode					
I_S	source (diode forward) current (DC)	T_{sp} = 25 °C	-	1.45	A
I_{SM}	peak source (diode forward) current	T_{sp} = 25 °C; pulsed; t_p ≤ 10 µs	-	5.95	A